

N-Ch 120V Fast Switching MOSFETs

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

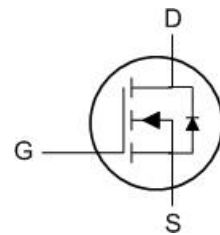
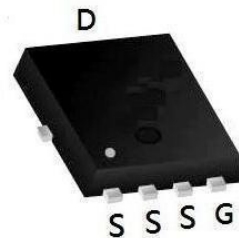
- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

Product Summary



BVDSS	RDSON	ID
120V	6.0mΩ	100A

PDFN5060-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	120	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	100	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	64	A
I_{DM}	Pulsed Drain Current ²	400	A
EAS	Single Pulse Avalanche Energy ³	326	mJ
I_{AS}	Avalanche Current	---	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	119	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	52	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.7	$^\circ C/W$

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	120	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	---	---	$V/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=21A$	---	6	7.5	$m\Omega$
		$V_{GS}=4.5V$, $I_D=10A$	---	6.5	8	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.4	1.8	2.2	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=120V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=120V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=21A$	---	---	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	0.84	---	Ω
Q_g	Total Gate Charge	$V_{DS}=60V$, $V_{GS}=10V$, $I_D=21A$	---	60.8	---	nC
Q_{gs}	Gate-Source Charge		---	18.8	---	
Q_{gd}	Gate-Drain Charge		---	14.7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=60V, I_D=21A$ $R_G=5\Omega$, $V_{GS}=10V$	---	20	---	ns
T_r	Rise Time		---	65	---	
$T_{d(off)}$	Turn-Off Delay Time		---	32	---	
T_f	Fall Time		---	49	---	
C_{iss}	Input Capacitance	$V_{DS}=60V$, $V_{GS}=0V$, $f=1MHz$	---	3614	---	pF
C_{oss}	Output Capacitance		---	423	---	
C_{rss}	Reverse Transfer Capacitance		---	12	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	100	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=21A$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=42A$, $di/dt=100A/\mu s$	---	60	---	nS
Q_{rr}	Reverse Recovery Charge	μs , $T_J=25^\circ\text{C}$	---	109	---	nC

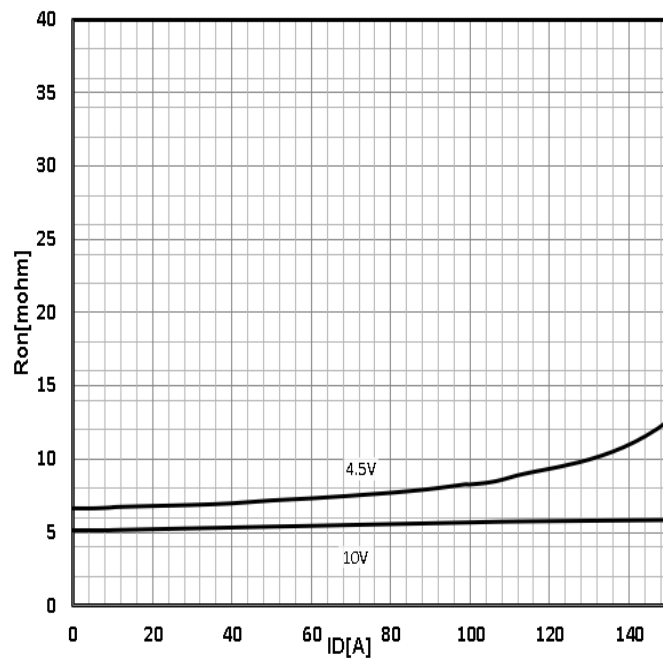
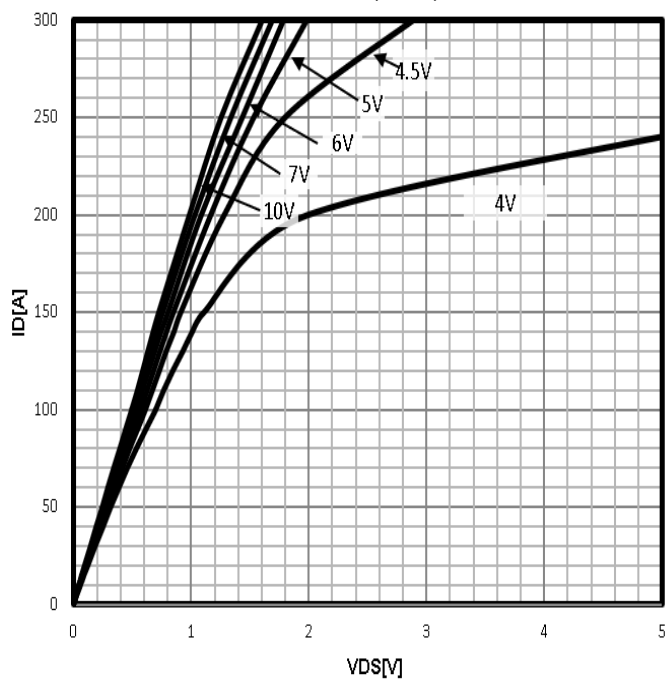
1.Repetitive rating; pulse width limited by maximum junction temperature

2. $V_{DD}=60V$, $L=0.5mH$, $R_g=25\Omega$, Starting $T_J=25^\circ\text{C}$

Characteristics Curve:

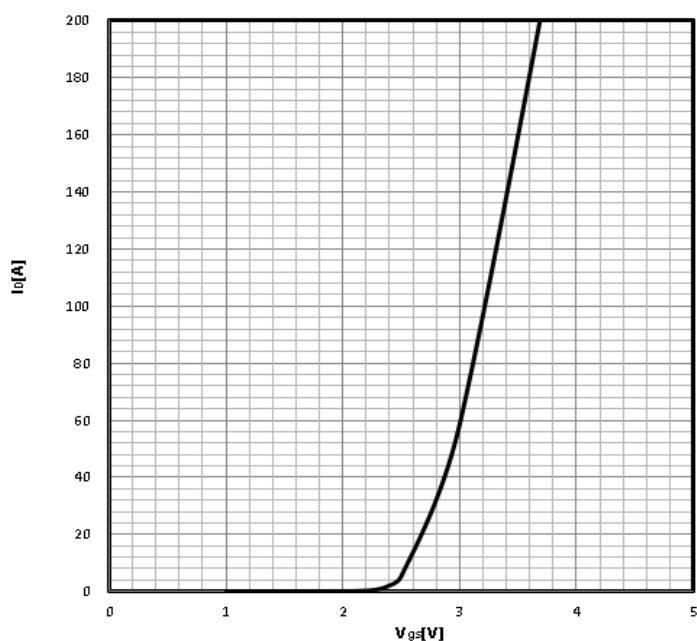
Typ. output characteristics

$$I_D = f(V_{DS})$$



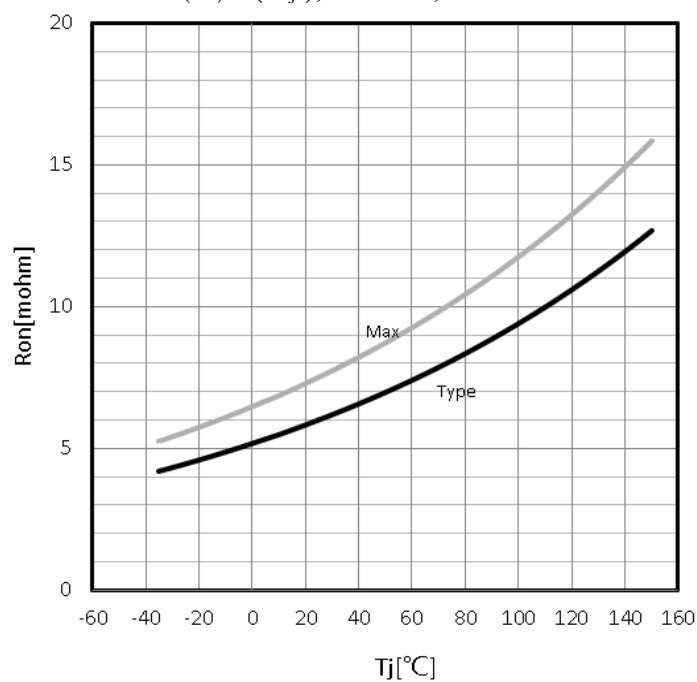
Typ. transfer characteristics

$$I_D = f(V_{GS})$$



Drain-source on-state resistance

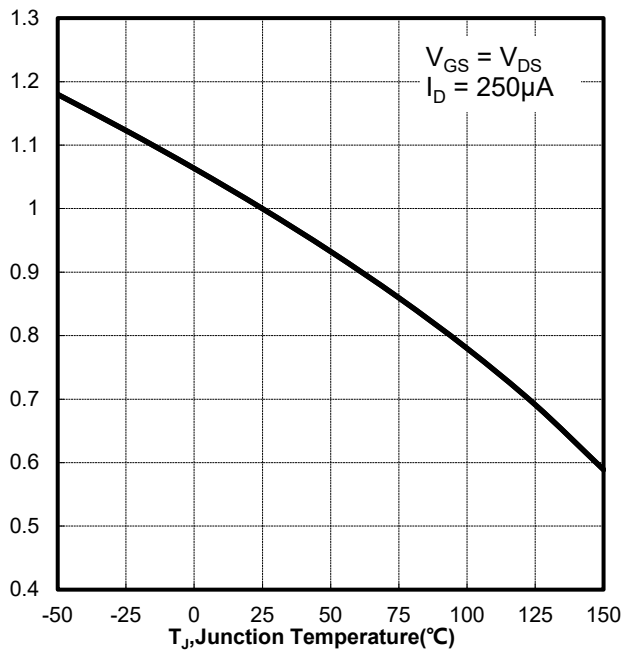
$$R_{DS(on)} = f(T_j); I_D = 20A; V_{GS} = 10V$$



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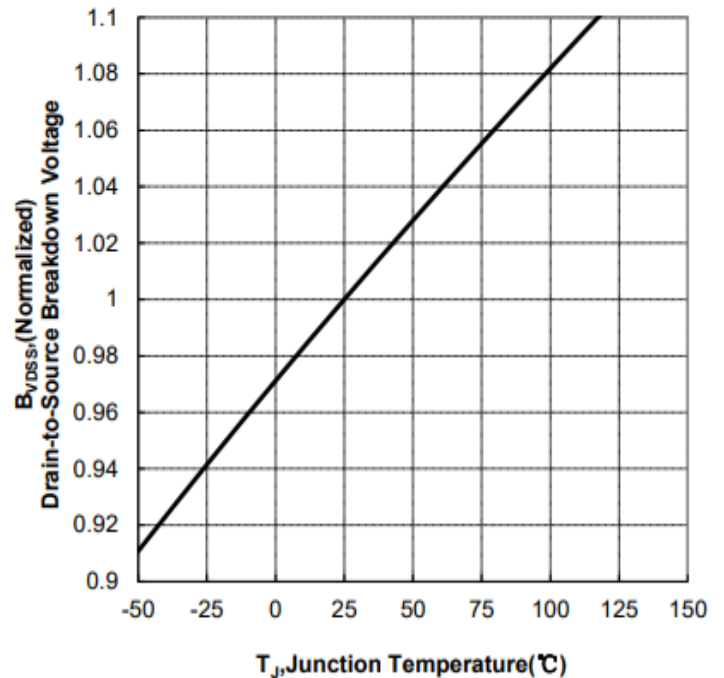
Gate Threshold Voltage

$$V_{TH}=f(T_j); I_D=250\mu A$$



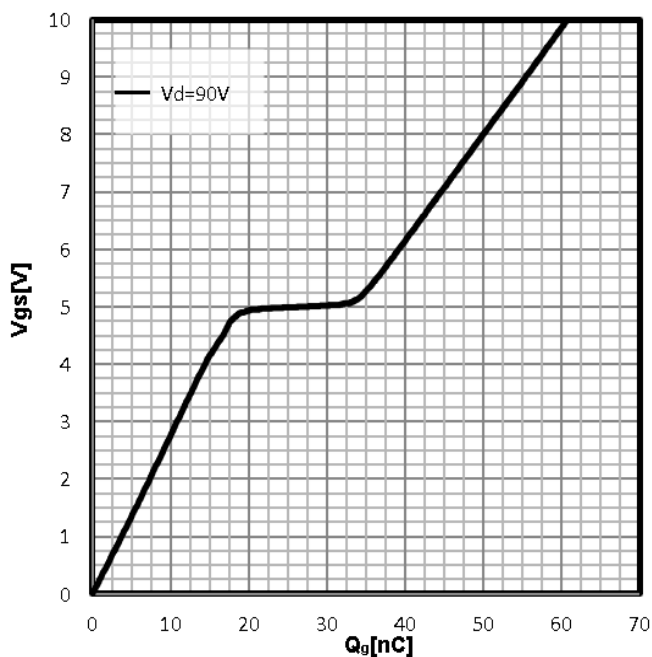
Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=250\mu A$$



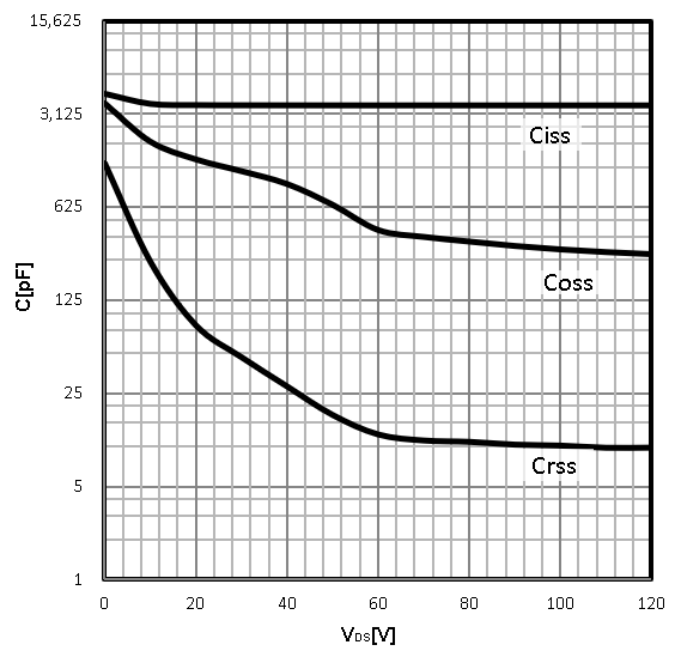
Typ. gate charge

$$V_{GS}=f(Q_{gate})$$



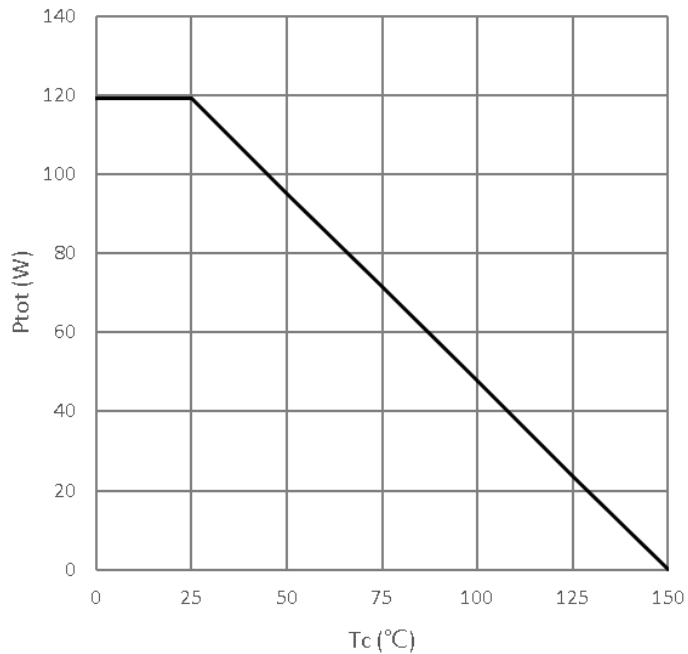
Typ. capacitances

$$C=f(V_{DS}); V_{GS}=0V; f=1MHz$$



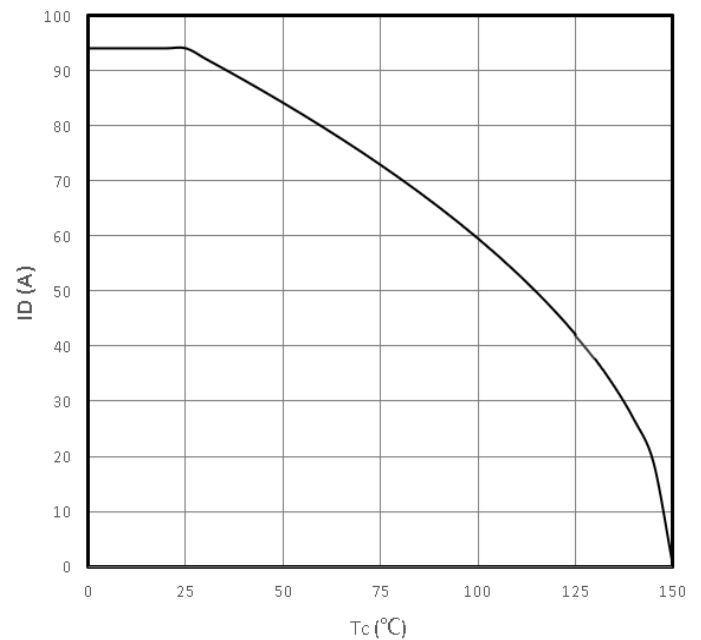
Power Dissipation

$$P_{tot}=f(T_j)$$



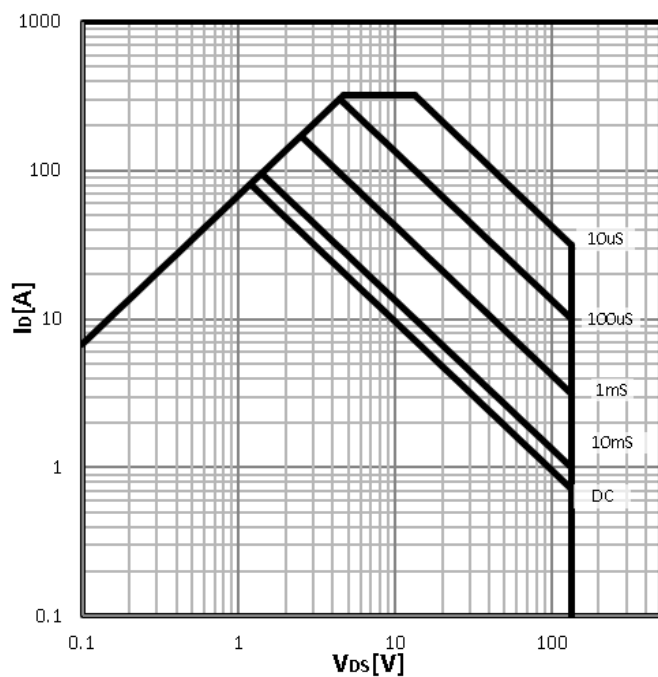
Maximum Drain Current

$$I_D=f(T_c)$$



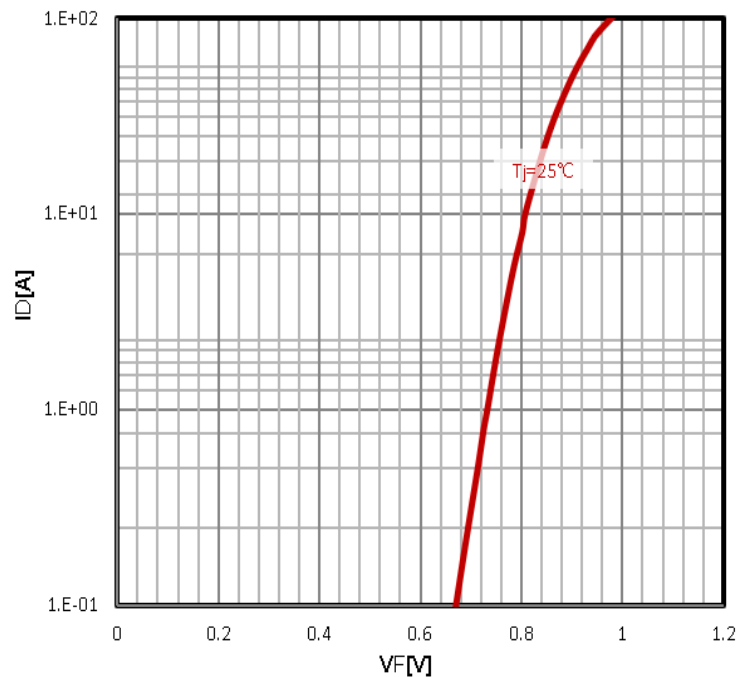
Safe operating area

$$I_D=f(V_{DS})$$



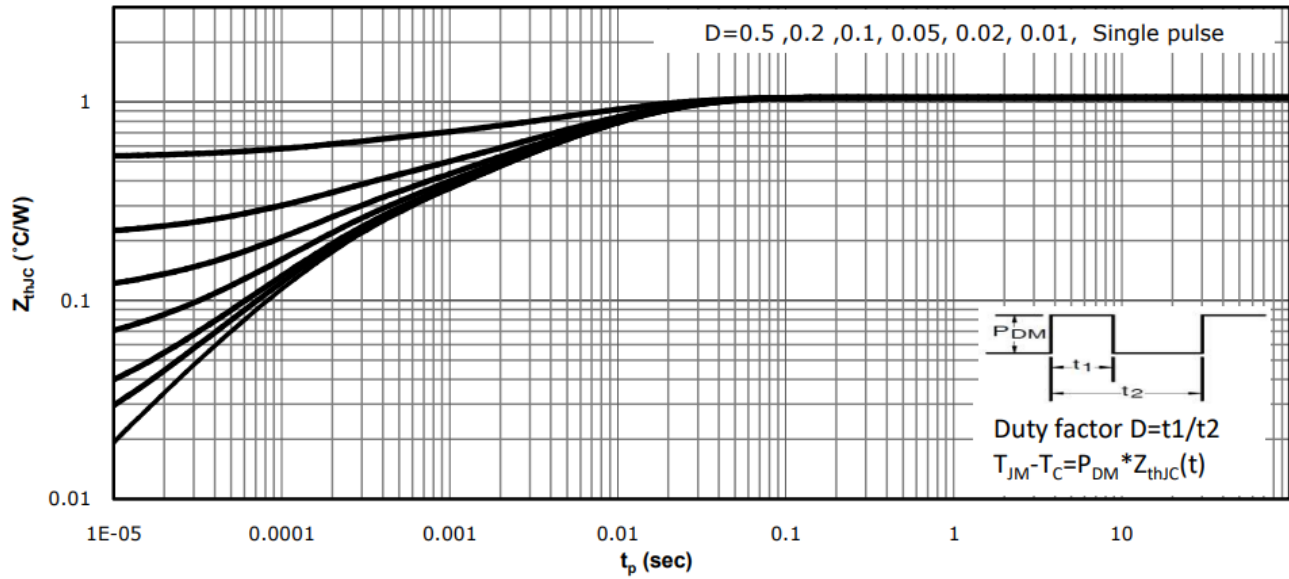
Body Diode Forward Voltage Variation

$$I_F=f(V_{GS})$$



Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$



Test Circuit

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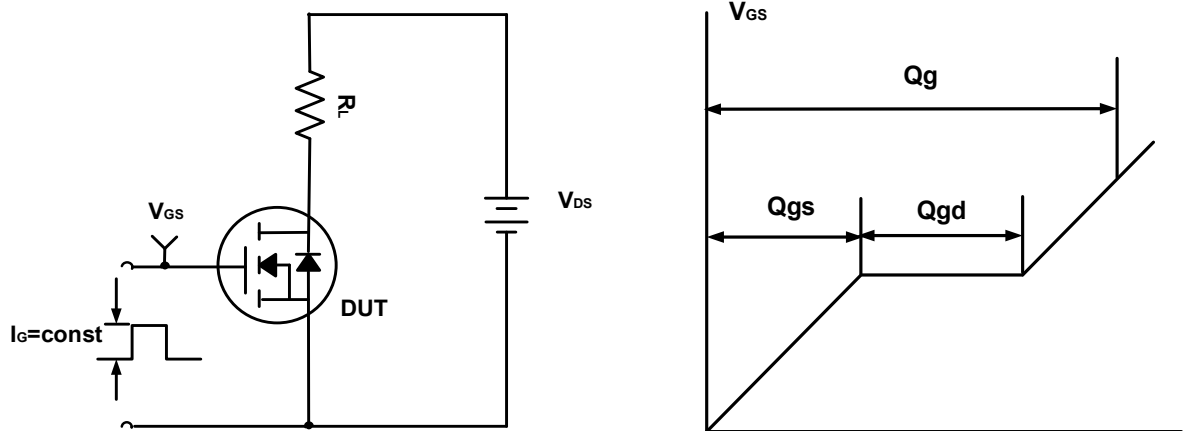


Figure A. Gate Charge Test Circuit & Waveforms

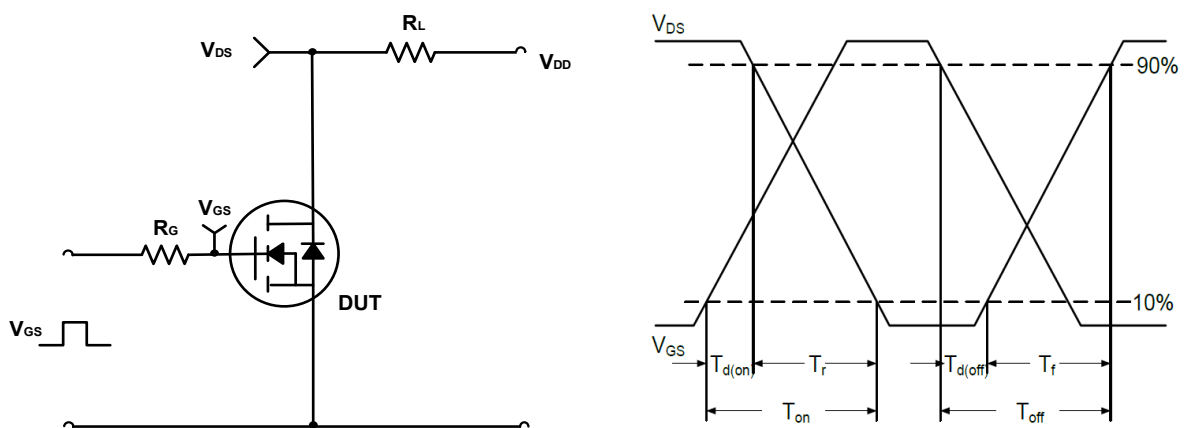


Figure B. Switching Test Circuit & Waveforms

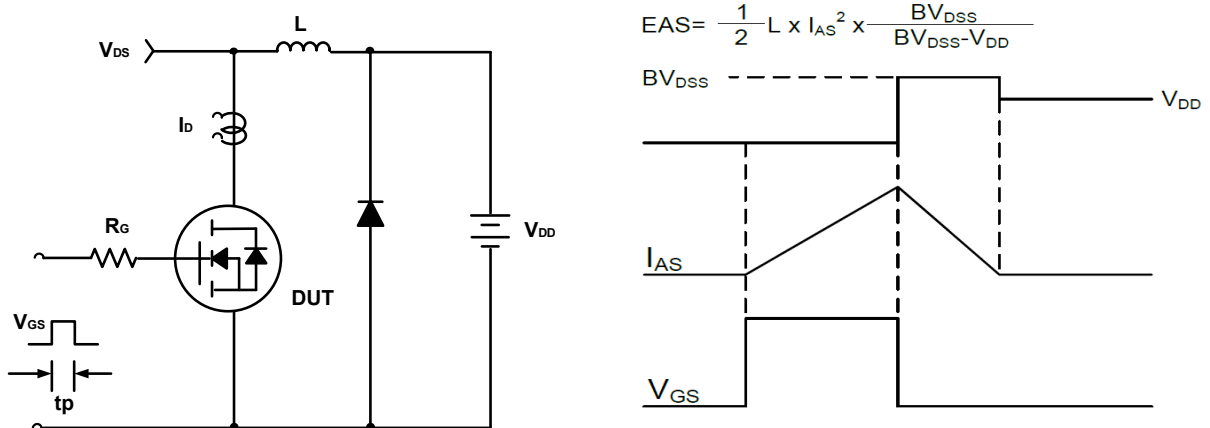
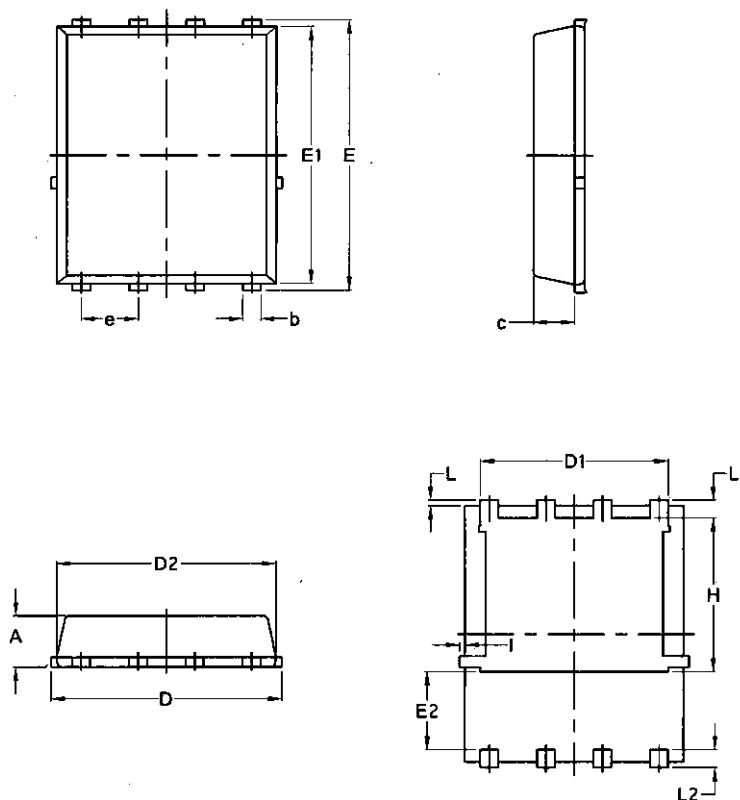


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Package Mechanical Data-PDFN5060-8L-Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070